

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application: Please cancel claim 1 without prejudice and amend claims 2, 4, 6 and 7 and add new claims 10-13 as follows:

LISTING OF CLAIMS:

1. (Cancelled)

2. (Currently Amended) ~~The~~ A semiconductor storage device ~~according to claim 1, comprising:~~

a nonvolatile memory to which data is written in a sector unit; and

a data rewriting unit rewriting data in the nonvolatile memory, wherein

each sector in said nonvolatile memory includes: a data area into which data is stored; and a refresh mark into which information indicative of whether refresh has been performed or not is stored, and

said data rewriting unit includes a refresh execution unit referring to said refresh mark and determining whether the sector is refreshed or not, thereby executing the refresh, wherein

said data rewriting unit further includes a refresh zone detection unit dividing a block of said nonvolatile memory into refresh zone units for executing refresh, and detecting the refresh zone including a sector of a writing target, and

said refresh execution unit refreshes the sector included in the refresh zone detected by said refresh zone detection unit every time data is written to a sector.

3. (Original) The semiconductor storage device according to claim 2, wherein every time data is written to a sector, said refresh execution unit sequentially refreshes the sectors included in the refresh zone detected by said refresh zone detection unit, starting at a head sector or a final sector, and sets a first value in the refresh mark included in the sector, and

after completion of the refreshes for all the sectors included in said refresh zone, every time data is written to a sector, said refresh execution unit sequentially refreshes the sectors included in the refresh zone detected by said refresh zone detection unit, starting at the head sector or the final sector, and sets a second value different from the first value in the refresh mark included in the sector.

4. (Currently Amended) ~~The~~ A semiconductor storage device according to claim 1, comprising:

a nonvolatile memory to which data is written in a sector unit; and

a data rewriting unit rewriting data in the nonvolatile memory, wherein

each sector in said nonvolatile memory includes: a data area into which data is stored; and a refresh mark into which information indicative of whether refresh has been performed or not is stored, and

said data rewriting unit includes a refresh execution unit referring to said refresh mark and determining whether the sector is refreshed or not, thereby executing the refresh, wherein

said data rewriting unit further includes a refresh zone detection unit dividing a block of said nonvolatile memory into refresh zone units for performing refresh, and detecting the refresh zone including a sector of a writing target, and

said refresh execution unit refreshes the sectors included in the refresh zone, every time data is written to a sector in the refresh zone detected by said refresh zone detection unit for a predetermined number of times.

5. (Original) The semiconductor storage device according to claim 4, wherein every time data is written to the sector in the refresh zone detected by said refresh zone detection unit for the predetermined number of times, said refresh execution unit sequentially refreshes the sectors included in the refresh zone, starting at a head sector or a final sector, and sets a first value in the refresh mark included in the sector, and

after completion of the refreshes for all the sectors included in said refresh zone, every time data is written to the sector in the refresh zone for the predetermined number of times, said refresh execution unit sequentially refreshes the sectors included in the refresh zone, starting at the head sector or the final sector, and sets a second value different from the first value in the refresh mark included in the sector.

6. (Currently Amended) The semiconductor storage device according to claim 4 2, wherein

each sector in said nonvolatile memory further includes a data error detection/correction code, and

when refreshing the sector, said refresh execution unit writes data corrected by using said data error detection/correction code to the sector.

7. (Currently Amended) The semiconductor storage device according to claim 4 2, wherein

each sector in said nonvolatile memory further includes a non-defective sector code indicating whether the sector is defective or not, and

when refreshing the sector, said refresh execution unit suspends the refresh in the case where the sector has been found to be a defective sector by referring to said non-defective sector code.

8. (Original) The semiconductor storage device according to claim 7, wherein in the case where the sector has been found to be a defective sector by referring to said non-defective sector code, said refresh execution unit refreshes another sector in said refresh zone.

9. (Original) The semiconductor storage device according to claim 7, wherein in the case where an error generates after the refresh for the sector and the sector has been found to be a defective sector by referring to said non-defective sector code, said refresh execution unit suspends the refresh.

10. (New) The semiconductor storage device according to claim 4, wherein each sector in said nonvolatile memory further includes a data error detection/correction code, and

when refreshing the sector, said refresh execution unit writes data corrected by using said data error detection/correction code to the sector.

11. (New) The semiconductor storage device according to claim 4, wherein each sector in said nonvolatile memory further includes a non-defective sector code indicating whether the sector is defective or not, and when refreshing the sector, said refresh execution unit suspends the refresh in the case where the sector has been found to be a defective sector by referring to said non-defective sector code.

12. (New) The semiconductor storage device according to claim 11, wherein in the case where the sector has been found to be a defective sector by referring to said non-defective sector code, said refresh execution unit refreshes another sector in said refresh zone.

13. (New) The semiconductor storage device according to claim 11, wherein in the case where an error generates after the refresh for the sector and the sector has been found to be a defective sector by referring to said non-defective sector code, said refresh execution unit suspends the refresh.